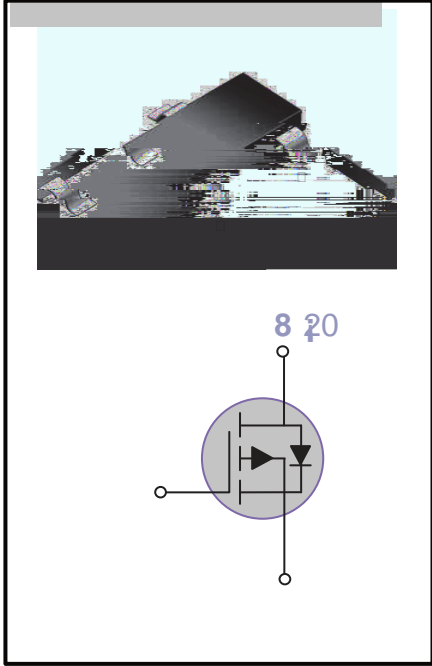




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ÓXÖÙÙ	ÜÖÙUÞ	QÖ
ËÎ€X	FJ€ { ô	ËGœ



- ' ËÎ€XËËGœËÁÜÖÙÇUÞDÁMFJ€ { OXÖÙÁMÄËF€X
- ' Improved dv/dt capability
- ' Fast switching
- ' Green Device Available

ÖÁGÍ»ÔÁCE { ää^}cÁV^ {]^!æc~!^ÁÇ~ }|^•• [c@^! , ä•^ } [c^âD

	Ö!æä}ËÙ [~!&^ÁX [cæ*^		XÁ
	Öæc^ËÙ [~f&^ÁX [cæ*^Á		XÁ
I _D	Ö!æä}ÁÔ~! !^}cÁ . ÁÔ [}cá} ~ [~•ÁÇV _o MGÍ °CDÁ	-2	œÁ
	Ö!æä}ÁÔ~! !^}cÁ . ÁÔ [}cá} ~ [~•ÁÇV _o MF€€ °CDÁ	-1.25	œÁ
I _{DM}	Ö!æä}ÁÔ~! !^}cÁ . ÁÚ~ •^âFÁ	-8	œÁ
P _D	Ú [, ^!ÁÔä••ä]æcá []ÁÇV _o MGÍ °CDÁ	1.56	YÁ
	Ú [, ^!ÁÔä••ä]æcá []Á . ÁÔ^!æc^Áæà [Ç^ÁGÍ °CÁ	0.012	Yß °CÁ
T _{STG}	Ùc [!æ*^ÁV^ {]^!æc~!^ÁÜæ} *^Á	-50 to 150	°C
T _J	U]^!æcá} *ÁR~ }&cá [}ÁV^ {]^!æc~!^ÁÜæ} *^Á	-50 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{JA}	Thermal Resistance Junction to ambient	---	80	°C/W



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Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25 $^{\circ}C, I_D=-1mA$	---	-0.05	---	
I_{DSS}	Drain-Source Leakage Current		---	---	-1	μA
			---	---	-10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-2A$	---	160	190	m
		$V_{GS}=-4.5V, I_D=-1.5A$	---	200	240	m
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	-1.9	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	5	---	
g_{fs}	Forward Transconductance	$V_{DS}=-10V, I_D=-2A$	---	3.5	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge ^{2,3}	$V_{DS}=-30V, V_{GS}=-10V, I_D=-2A$	---	8.2	12	nC
Q_{gs}	Gate-Source Charge ^{2,3}		---	1.8	3.6	
Q_{gd}	Gate-Drain Charge ^{2,3}		---	1.5	3	

$T_{d(on)}$ Turn-On Delay Time^{2,3}

$V_{DD}=-30V, V_{GS}=-10V, R_G=6$

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